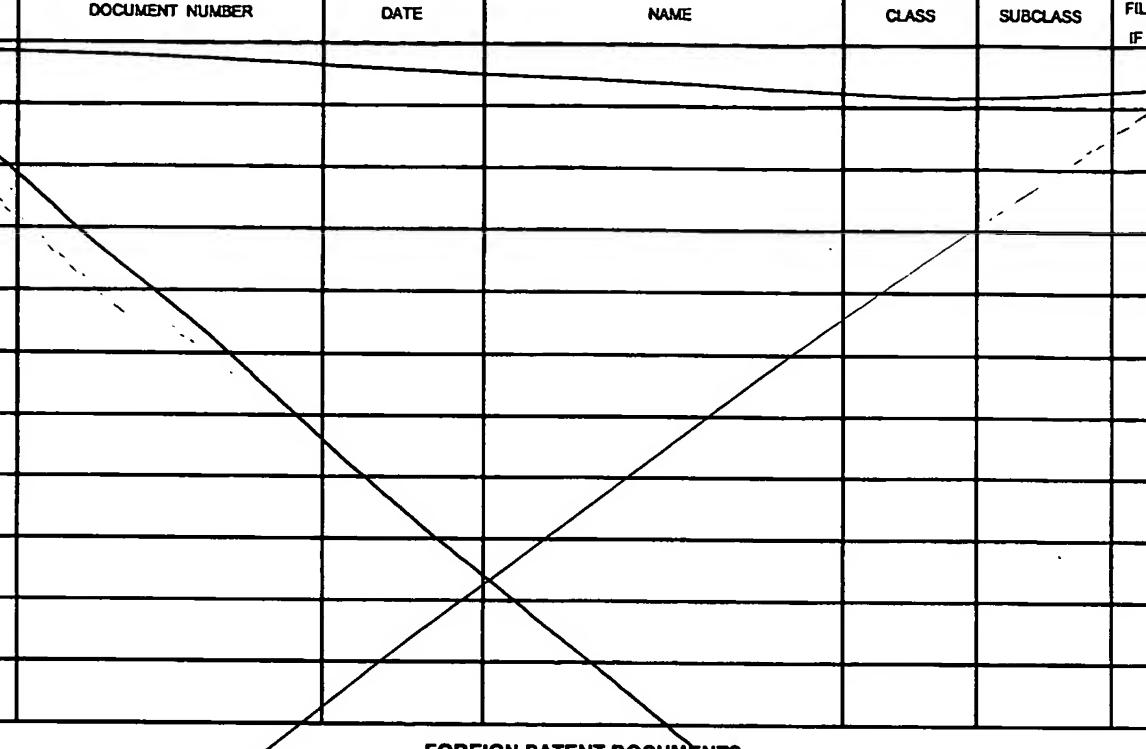
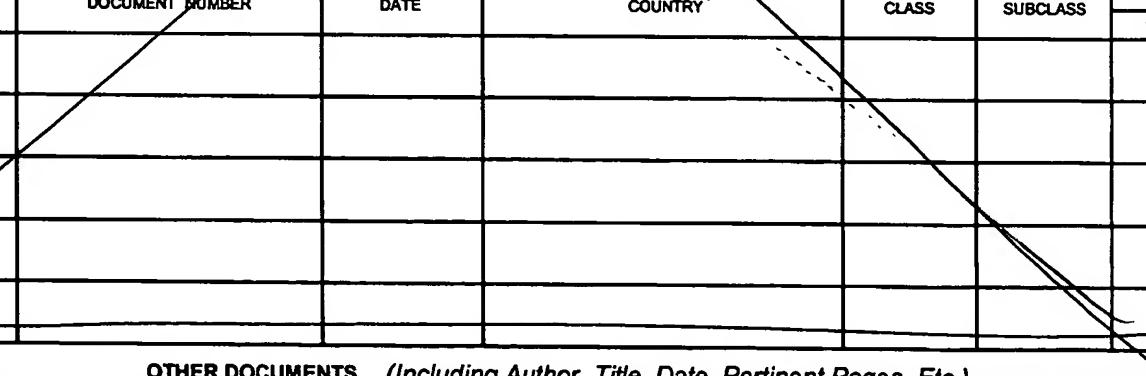
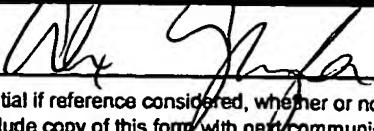


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				Alessandro Callegari, et al.			
				FILING Herewith	GROUP Unassigned		
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL <i>AC</i>	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	5,312,565	11/01	Misra, et al.				
	6,037,003	3/14/00	Gordon, et al.				
	5,728,222	3/17/98	Barbee, et al.				
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	4,097,314	6/27/78	Schlesier, et al.				
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
<i>AC</i>		Eble, R., et al., "Low Temperature Aluminum Oxide Deposition Using Trimethylaluminum", <u>Journal of Electronic Materials</u>, Vol. 12, No. 3, pp. 587-601 (1983);					
<i>AC</i>		Kim, J.S., et al., "Fabrication of Aluminum Oxide Thin Films by a Low-Pressure Metalorganic Chemical Vapor Deposition Technique", <u>App. Phys. Lett.</u>, 62(7), February 15, 1993;					
EXAMINER <i>AC</i>			DATE CONSIDERED <i>9/27/05</i>				
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FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
								
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
			Fournier, J., et al., "Preparation and Characterization of Thin Films of Alumina by Metal-Organic Chemical Vapor Deposition", <u>Mat. Res. Bull.</u> , Vol. 23, pp. 31-36, 1988;					
			Klein, T.M., et al. "Evidence of Aluminum Silicate Formation During Chemical Vapor Deposition of Amorphous Al ₂ O ₃ Thin Films on Si (100)", <u>Applied Physics Letters</u> , Vol. 75, No. 25, pp. 4001-4003, 1999;					
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>AC</i>		Lo, S.-H, et al., "Quantum-Mechanical Modelling of Electron Tunneling Current From the Inversion Layer of Ultra-Thin-Oxide nMOSFET's", <u>IEEE Electron Device Letters</u> , Vol. 18, No. 5, pp. 209-211, May 1997;					
<i>AC</i>		Mutoh, H., et al., "Multilayer Metallization with Planar Interconnect Structure Utilizing CVD Al2O3 Film", <u>J. Electrochem. Soc.: SOLID-SCIENCE AND TECHNOLOGY</u> , Vol. 12, No. 7, pp. 987-992, July 1975; and					
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES
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<i>AC</i>	<i>Yom, S.S., et al., "Growth of -A12O3 Thin Films on Silicon by Low Pressure Metal-Organic Chemical Vapour Deposition", Elsevier Sequoia, 213, pp. 72-75, 1992.</i>	<i>9/27/05</i>				
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